#3

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
M4065.019/[illegible]	~~Not Yet Assigned~~ 09/750111
Applicant(s)	
Wendell P. Noble, Jr., et al.	
Filing Date	**Group Art Unit**
Concurrently Herewith	N/A

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPR PRIATE
KR		5,173,754	12/1992	M. Manning			
		5,214,295	05/1993	M. Manning			
		5,286,663	02/1994	M. Manning			
		5,486,717	01/1996	Kokubo et al.			
		5,497,011	03/1996	T. Terashima			
		5,535,156	07/1996	Levy et al.			
		5,581,104	12/1996	Lowrey et al.			
		5,594,683	01/1997	Chen et al.			
		5,624,863	04/1997	Helm et al.			
		5,650.350	07/1997	Dennison et al.			
KR		5,705,843	01/1998	M. C. Roberts			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

KR		R. C. Fang, LATCHUP MODEL FOR THE PARASITIC P-N-P-N PATH IN BULK CMOS, IEEE Transactions on Electron Devices, Vol. Ed. 31, No. 1, January 1984,
KR		R. R. Troutman et al, TRANSIENT ANALYSIS OF LATCHUP IN BULK CMOS, IEEE Transactions on Electron Devices, Vol. Ed. 30, No. 2, February 1993

EXAMINER	DATE CONSIDERED
Not Yet Assigned [signature]	2/26/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
~~M4065.019/P019~~	~~Not Yet Assigned~~ 09/750111
Applicant(s)	
Wendell P. Noble, Jr., et al.	
Filing Date	**Group Art Unit**
Concurrently Herewith	N/A

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		5,710,741	01/1998	L. McLaury			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

KR		D. L. Hetherington ET AL, AN INTEGRATED GaAs N-P-N-P THYRISTOR/JFET MEMORY CELL EXHIBITING NONDESTRUCTIVE READ, IEEE Electron Device Letters, Vol. 13, No. 9, September 1992
KR		S. V. Vandebroek et al, HIGH-GAIN LATERAL BIPOLAR ACTION IN A MOSFET STRUCTURE, IEEE Transactions on Electron Devices, Vol. 38, No. 11, November 1991

EXAMINER	DATE CONSIDERED
Not Yet Assigned	2/26/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

Docket Number	Application Number
M4065.019/P019	~~Not Yet Assigned~~ 09/750111
Applicant(s)	
Wendell P. Noble, Jr., et al.	
Filing Date	Group Art Unit
Concurrently Herewith	Not Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	No Citations to United States Patent Documents						

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT	DATE	NAME	CLASS	SUBCLASS	Translations YES	Translations NO
	No Citations to Foreign Patent Documents							

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

KR		Dermot MacSweeney et al., MODELING OF LATERAL BIPOLAR DEVICES IN A CMOS,
		IEEE BCTM 1.4, 4 pages
		J.J. Ebers, FOUR-TERMINAL P-N-P-N TRANSISTORS, Proceedings of IRE, Nov. 1952, p.1361-4
		I.T. HO et al, SINGLE THYRISTOR STATIC MEMORY AND ITS FABRICATION, Vol. 23, No.3, 1980
		B.L. Gregory et al, LATCHUP IN CMOS INTEGRATED CIRCUITS, Sandia Laboratories, p.12-18
		S. M. Sze, PHYSICS OF SEMICONDUCTOR DEVICES, Second Edition, A Wiley Interscience Pub.
		S.D. Malaviya, SINGLE-DEVICE DC STABLE MEMORY CELL, IBM Technical Disclosure Bulletin,
KR		Vol. 20, No. 9, pp 3492-94, November 1978.

EXAMINER Not Yet Assigned DATE CONSIDERED 2/26/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.